



JRW

Patent
Attorney's Docket No. H1492

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Bin Yu et al.) Group Art Unit: 2829
Application No.: 10/653,105) Examiner: S. Geyer
Filed: September 3, 2003)
For: ADDITIONAL GATE CONTROL)
FOR A DOUBLE-GATE MOSFET)

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
TRANSMITTAL LETTER

U.S. Patent and Trademark Office
220 20th Street S.
Customer Window, Mail Stop Amendment
Crystal Plaza Two, Lobby, Room 1B03
Arlington, Virginia 22202

Sir:

Enclosed is a Supplemental Information Disclosure Statement and accompanying form PTO-1449 for the above-identified patent application.

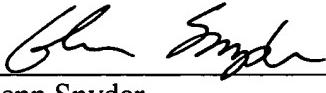
- No additional fee for submission of the IDS is required.
- The fee of \$180.00 as set forth in 37 C.F.R. § 1.17(p) is also enclosed.
- A certification under 37 C.F.R. § 1.97(e) is also enclosed.
- Charge \$ _____ to Deposit Account No. 50-1070 for the fee due.
- A check in the amount of \$ _____ is enclosed for the fee due.

Supplemental Information Disclosure Statement Transmittal Letter
Application Serial No. 10/653,105
Attorney's Docket No. H1492
Page 2

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R.
§§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to
Deposit Account No. 50-1070.

Respectfully submitted,

HARRITY & SNYDER, L.L.P.

By: 
Glenn Snyder
Reg. No. 41,428

11240 Waples Mill Road
Suite 300
Fairfax, Virginia 22030
(571) 432-0800
Customer Number: 26615

Date: July 26, 2004



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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. § 1.97(c)

U.S. Patent and Trademark Office
220 20th Street S.
Customer Window, Mail Stop Amendment
Crystal Plaza Two, Lobby, Room 1B03
Arlington, Virginia 22202

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(c), applicant(s) bring(s) to the attention of the Examiner the documents listed on the attached PTO 1449. This Supplemental Information Disclosure Statement is being filed after the events recited in Section 1.97(b) but, to the undersigned's knowledge, before the mailing date of either a Final Action or a Notice of Allowance. Under the provisions of 37 C.F.R. § 1.97(c), this Supplemental Information Disclosure Statement:

includes a certification as specified by Section 1.97(e).

is accompanied by a fee of \$180.00 as specified by Section 1.17(p).

Supplemental Information Disclosure Statement Under 37 C.F.R. § 1.97(c)
Application Serial No. 10/653,105
Attorney's Docket No. H1492
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Certification 1: Each item of information contained in the Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.

Certification 2: No item of information contained in the Supplemental Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the Supplemental Information Disclosure Statement was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing date of the Supplemental Information Disclosure Statement.

Copies of the non-patent documents are attached.

Copies of the listed documents were previously submitted in a prior application, serial no. _____, filing date _____, upon which applicant(s) rely(ies) for the benefits provided in 35 U.S.C. § 120. Applicant(s) respectfully request(s) that the Examiner consider the listed documents and indicate that they were considered by making appropriate notations on the attached form.

The following is a concise statement of relevance of the non-English language documents.

1. _____ discloses _____.

2. _____ discloses _____.

English translations of the non-English documents are enclosed.

In lieu of a statement of relevance or translation of the non-English documents, an English language version of a search report from the _____ Patent Office in a corresponding application citing these documents and setting forth the relevance thereof is enclosed.

Supplemental Information Disclosure Statement Under 37 C.F.R. § 1.97(c)
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This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claims in the application and applicant(s) determine(s) that the cited document(s) do not constitute "prior art" under United States law, applicant(s) reserve(s) the right to present to the office the relevant facts and law regarding the appropriate status of such documents.

Applicant(s) further reserve(s) the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

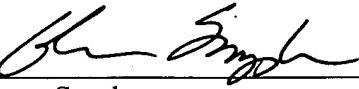
If any copending application(s) is/are cited on the attached PTO 1449, the Examiner's attention is directed to the foregoing application(s) in compliance with § 2001.06(b) of the Manual of Patent Examining Procedure. By identifying the copending application(s), the assignee and/or applicant of the application(s) do not waive confidentiality of the application(s). Accordingly, the U.S. Patent and Trademark Office is requested to maintain the confidentiality of the copending application(s) under 35 U.S.C. § 122.

Supplemental Information Disclosure Statement Under 37 C.F.R. § 1.97(c)
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If there is any fee due in connection with the filing of this Statement, please charge the
fee to our Deposit Account No. 50-1070.

Respectfully submitted,

HARRITY & SNYDER, L.L.P.

By: 
Glenn Snyder
Reg. No. 41,428

11240 Waples Mill Road
Suite 300
Fairfax, Virginia 22030
(571) 432-0800
Customer Number: 26615

Date: July 26, 2004

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SHEET 1 OF 1

**INFORMATION
DISCLOSURE
CITATION**
PTO-1449

PATENT TRADEMARK OFFICE

Customer Number
26615ATTORNEY'S DKT NO.
H1492APPLICATION NO.
10/653,105APPLICANT(S)
Bin Yu et al.FILING DATE
September 3, 2003GROUP
2829

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	US 2002/0125536 A1	09-12-02	Iwasa et al.	257	368	07-18-01
	US 2002/0153587 A1	10-24-02	Adkisson et al.	257	510	07-02-02
	US 2002/0177263 A1	11-28-02	Hanafi et al.	438	183	05-24-01
	6,359,311 B1	03-19-02	Colinge et al.	257	347	01-17-01

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Jong-Tae Park et al.: "Multiple-Gate SOI MOSFETs: Device Design Guidelines," <i>IEEE Transactions on Electron Devices</i> , Vol. 49, No. 12, December 2002, pp. 2222-2229.
	Fu-Liang Yang et al.: "25 nm CMOS Omega FETs," International Electron Devices Meeting 2002, IEDM, Technical Digest, December 8-11, 2002 in New York, NY, pp. 255-258.
	Toshikazu Mukaiyama et al.: "Fabrication of Gate-All-Around MOSFET By Silicon Anisotropic Etching Technique," <i>Solid State Electronics</i> , Elsevier Science Publishers, Vol. 42, No. 7-8, July 8, 1998, pp. 1623-1626.
	Yang-Kyu Choi et al.: "Spacer FinFET: nanoscale double-gate CMOS technology for the terabit era," <i>Solid State Electronics</i> , Elsevier Science Publishers, Vol. 46, No. 10, October 2002, pp. 1595-1601.
	Effendi Leobandung et al.: "Wire-channel and wrap-around-gate metal-oxide-semiconductor field-effect transistors with a significant reduction of short channel effects," 41 st International Conference on Electron, Ion, and Photon Beams Technology and Nanofabrication in Dana Point, CA, May 27-30, 1997, Vol. 15, No. 6, <i>Journal of Vacuum Science & Technology B</i> (Microelectronics and Nanometer Structures), November-December 1997, AIP for American Vacuum Soc., pp. 2791-2794.
	PCT International Search Report mailed July 13, 2004, 5 pages.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).